

High Performance Driver/Comparator Active Load on a Single Chip

AD53032

FEATURES

250 MHz Operation
Driver/Comparator and Active Load Included
On-Chip Schottky Diode Bridge
52-Lead LQFP Package with Built-in Heatsink

APPLICATIONS
Automatic Test Equipment
Semiconductor Test Systems
Board Test Systems
Instrumentation and Characterization Equipment

PRODUCT DESCRIPTION

The AD53032 is a single chip that performs the pin electronics functions of driver, comparator and active load in ATE VLSI and memory testers. In addition, a Schottky diode bridge for the active load and a VCOM buffer are included internally.

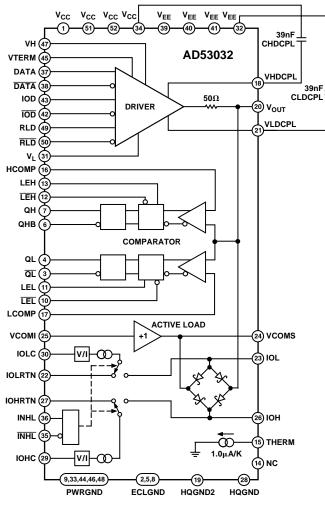
The driver is a proprietary design that features three active states: Data High Mode, Data Low Mode and Term Mode as well as an Inhibit State. This facilitates the implementation of high speed active termination. The output voltage range is -3 V to +8 V to accommodate a wide variety of test devices. The output leakage is typically less than 250 nA over the entire signal range.

The dual comparator, with an input range equal to the driver output range, features built-in latches and ECL-compatible outputs. The outputs are capable of driving 50 Ω signal lines terminated to -2 V. Signal tracking capability is upwards of 5 V/ns.

The active load can be set for up to 35 mA load current with less than a 10 μ A linearity error through the entire set range. $I_{OH},\ I_{OL}$ and the buffered VCOM are independently adjustable. Onboard Schottky diodes provide high speed switching and low capacitance.

Also included on the chip is an onboard temperature sensor whose purpose is to give an indication of the surface temperature of the DCL. This information can be used to measure θ_{JC} and θ_{JA} or flag an alarm if proper cooling is lost. Output from the sensor is a current sink that is proportional to absolute temperature. The gain is trimmed to a nominal value of 1.0 $\mu A/K$. As an example, the output current can be sensed by using a 10 k Ω resistor connected from +10 V to the THERM (IOUT) pin. A voltage drop across the resistor will be developed that equals: $10K\times 1~\mu A/K=10~mV/K=2.98~V$ at room temperature.

FUNCTIONAL BLOCK DIAGRAM



NC = NO CONNECT

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AD53032—SPECIFICATIONS

DRIVER SPECIFICATIONS

(All specifications are at $T_J = +85^{\circ}\text{C} \pm 5^{\circ}\text{C}$, $+V_S = +12 \text{ V} \pm 3\%$, $-V_S = -7 \text{ V} = \pm 3\%$ unless otherwise noted. All temperature coefficients are measured at $T_J = +75^{\circ}\text{C}$ to $+95^{\circ}\text{C}$). CHDCPL = CLDCPL = 39 nF.

Parameter	Min	Тур	Max	Units	Test Conditions
DIFFERENTIAL INPUT CHARACTERISTICS (DATA to DATA, IOD to IOD, RLD to RLD) Input Voltage	-2	FOL	0	V	
Differential Input Range Bias Current	-250	ECL	+250	μΑ	$V_{IN} = -2 \text{ V}, 0.0 \text{ V}$
REFERENCE INPUTS					
Bias Currents	-50		+50	μΑ	$V_L, V_H, V_T = 5 V$
OUTPUT CHARACTERISTICS					
Logic High Range	-2		8	V	DATA = H, V_H = -2 V to +8 V V_L = -3 V (V_H = -2 V to +6 V) V_L = -1 V (V_H = +6 V to +8 V)
Logic Low Range	-3		5	V	DATA = L, $V_L = -3 \text{ V to } +5 \text{ V}, V_H = +6 \text{ V}$
Amplitude (V_H and V_L) Absolute Accuracy	0.1		9	V	$egin{array}{l} V_L = 0.0 \ V, \ V_H = +0.1 \ V, \ V_T = 0 \ V \ V_L = -2 \ V, \ V_H = +7 \ V, \ V_T = 0 \ V \end{array}$
V _H Offset	-50		+50	mV	DATA = H, $V_H = 0 V$, $V_L = -3 V$, $V_T = +3 V$
V _H Gain + Linearity Error	0.3 – 5		+0.3 + 5	% of V _H + mV	DATA = H, $V_H = -2 V$ to +8 V, $V_L = -3 V$, $V_T = +3 V$
$ m V_L$ Offset $ m V_L$ Gain + Linearity Error	-50 -0.3 - 5		+50 +0.3 + 5	mV % of $V_L + mV$	DATA = L, $V_L = -3 V$, $V_H = +6 V$, $V_T = +7.5 V$ DATA = L, $V_L = 0 V$, $V_H = +6 V$, $V_T = +7.5 V$
Offset TC Output Resistance	0.5	0.5	10.5 1 5	mV/°C	$V_L = 0 \text{ V}, V_H = +5 \text{ V}, V_T = 0 \text{ V}$
Output Resistance $V_H = -2 \text{ V}$	44	46	48	Ω	$V_{\rm L} = -3 \text{ V}, V_{\rm T} = 0 \text{ V}, I_{\rm OUT} = 0, +1, +30 \text{ mA}$
$V_H = +8 \text{ V}$	44	46	48	Ω	$V_L = -1 \text{ V}, V_T = 0 \text{ V}, I_{OUT} = 0, -1, -30 \text{ mA}$
$V_L = -3 \text{ V}$	44	46	48	Ω	$V_H = +6 \text{ V}, V_T = 0 \text{ V}, I_{OUT} = 0, +1, +30 \text{ mA}$
$V_L = +5 V$	44	46	48	Ω	$V_H = +6 \text{ V}, V_T = 0 \text{ V}, I_{OUT} = 0, -1, -30 \text{ mA}$
$V_H = +3 V$		46		Ω	$V_L = 0 \text{ V}, V_T = 0 \text{ V}, I_{OUT} = -30 \text{ mA (Trim Point)}$
Dynamic Current Limit	100			mA	$C_{BYP} = 39 \text{ nF}, V_H = +7 \text{ V}, V_L = -2 \text{ V}, V_T = 0 \text{ V}$
Static Current Limit	-85		+85	mA	Output to -3 V, $V_H = +8$ V, $V_L = -1$ V, $V_T = 0$ V DATA = H and Output to $+8$ V, $V_H = +6$ V, $V_L = -3$ V, $V_T = 0$ V, DATA = L
$\overline{ m V}_{ m TERM}$					
Voltage Range	-3		8.0	V	TERM MODE, $V_T = -3 \text{ V to } +8 \text{ V}, V_L = 0 \text{ V}, V_H = 3 \text{ V}$
V _{TERM} Offset	-50		+50	mV	TERM MODE, $V_T = 0 \text{ V}$, $V_L = 0 \text{ V}$, $V_H = 3 \text{ V}$
$ m V_{TERM}$ Gain + Linearity Error	-0.3 + 5		+0.3 + 5	% of V_{SET} + mV	TERM MODE, $V_T = -3 \text{ V to } +8 \text{ V}, V_L = 0 \text{ V}, V_H = 3 \text{ V}$
Offset TC		0.5		mV/°C	$V_T = 0 \text{ V}, V_L = 0 \text{ V}, V_H = 3 \text{ V}$
Output Resistance	44	46	49	Ω	$\begin{split} &I_{OUT} = +30 \text{ mA}, +1.0 \text{ mA}, V_T = -3.0 \text{ V}, V_H = 3 \text{ V}, V_L = 0 \text{ V} \\ &I_{OUT} = -30 \text{ mA}, -1.0 \text{ mA}, V_T = +8.0 \text{ V}, V_H = 3 \text{ V}, V_L = 0 \text{ V} \\ &I_{OUT} = \pm 30 \text{ mA}, \pm 1.0 \text{ mA}, V_T = 0 \text{ V}, V_H = 3 \text{ V}, V_L = 0 \text{ V} \end{split}$
DYNAMIC PERFORMANCE, $(V_H \text{ AND } V_L)$	1.1	1.6	2.1		M 1 . 700/ W - 1400 W W - 400 W
Propagation Delay Time Propagation Delay TC	1.1	1.6 2	2.1	ns ps/°C	Measured at 50%, $V_H = +400 \text{ mV}$, $V_L = -400 \text{ mV}$ Measured at 50%, $V_H = +400 \text{ mV}$, $V_L = -400 \text{ mV}$
Delay Matching, Edge to Edge		<100		ps/ C ps	Measured at 50%, $V_H = +400 \text{ mV}$, $V_L = -400 \text{ mV}$ $V_L = -400 \text{ mV}$
Rise and Fall Times		1100		Po	intensification of the state of
1 V Swing		0.6		ns	Measured 20%–80%, $V_L = 0 \text{ V}$, $V_H = 1 \text{ V}$
3 V Swing		1.0		ns	Measured 20%–80%, $V_L = 0 V$, $V_H = 3 V$
5 V Swing		1.7		ns	Measured 10%–90%, $V_L = 0 \text{ V}$, $V_H = 5 \text{ V}$
9 V Swing		3.0		ns	Measured 10%–90%, $V_L = -2 \text{ V}$, $V_H = 7 \text{ V}$
Rise and Fall Time Temperature Coefficient		⊥ 1		ps/°C	Measured 20%–80%, $V_{L} = 0 \text{ V}$, $V_{H} = 1 \text{ V}$
1 V Swing 3 V Swing		±1 ±2		ps/°C ps/°C	Measured 20%–80%, $V_L = 0 \text{ V}$, $V_H = 1 \text{ V}$ Measured 20%–80%, $V_I = 0 \text{ V}$, $V_H = 3 \text{ V}$
5 V Swing		± 4		ps/°C	Measured $10\%-90\%$, $V_L = 0 \text{ V}$, $V_H = 5 \text{ V}$
Overshoot and Preshoot	-3.0 - 50		+3.0 + 50	% of Step + mV	$V_L, V_H = -0.1 \text{ V}, 0.1 \text{ V}, V_L, V_H = 0.0 \text{ V}, 1.0 \text{ V}$
					$V_L, V_H = 0.0 \text{ V}, 3.0 \text{ V}, V_L, V_H = 0.0 \text{ V}, 5.0 \text{ V}$ $V_L, V_H = -2.0 \text{ V}, 7.0 \text{ V}$
Settling Time					11) TH = -2.0 T, 1.0 T
to 15 mV		<50		ns	$V_L = 0 \text{ V}, V_H = 0.5 \text{ V}$
to 4 mV		<10		μs	$V_L = 0 \text{ V}, V_H = 0.5 \text{ V}$

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Parameter	Min	Тур	Max	Units	Test Conditions
Delay Change vs. Pulsewidth		<50		ps	$V_{L} = 0 \text{ V}, V_{H} = 2 \text{ V}$
Minimum Pulsewidth					
3 V Swing		2		ns	$V_L = 0 \text{ V}, V_H = 3 \text{ V}, 90\% \text{ Reached, Measure @ 50\%}$
5 V Swing		3		ns	$V_L = 0 \text{ V}, V_H = 5 \text{ V}, 90\% \text{ Reached, Measure } @ 50\%$
Toggle Rate		250		MHz	$V_L = 0 \text{ V}, V_H = 5 \text{ V}, VDUT > 3.0 \text{ V p-p}$
DYNAMIC PERFORMANCE, INHIBIT					
Delay Time, Active to Inhibit	1.5		4.0	ns	Measured at 50%, $V_H = +2 \text{ V}$, $V_L = -2 \text{ V}$
Delay Time, Inhibit to Active	1.5		3.5	ns	Measured at 50%, $V_H = +2 \text{ V}$, $V_L = -2 \text{ V}$
			± 1.0	ns	
Delay Time Matching (Z)			2.2	ns	Z = Delay Time Active to Inhibit Test (Above)—
					Delay Time Inhibit to Active Test (Above)
					(Of Worst Two Edges)
I/O Spike		<200		mV, p-p	$V_H = 0 V$, $V_L = 0 V$
Rise, Fall Time, Active to Inhibit			3.5	ns	$V_{\rm H}$ = +2 V, $V_{\rm L}$ = -2 V (Measured 20%/80% of 1 V Output)
Rise, Fall Time, Inhibit to Active			2.2	ns	$V_H = +2 \text{ V}, V_L = -2 \text{ V} \text{ (Measured 20\%/80\% of 1 V Output)}$
DYNAMIC PERFORMANCE , V _{TERM}					
Delay Time, V _H to V _{TERM}			3.0	ns	Measured at 50%, $V_L = V_H = +0.4 \text{ V}$, $V_{TERM} = -0.4 \text{ V}$
Delay Time, V _L to V _{TERM}			5.0	ns	Measured at 50%, $V_L = V_H = +0.4 \text{ V}$, $V_{TERM} = -0.4 \text{ V}$
Delay Time, V _{TERM} to V _H and V _{TERM} to V _L			4.0	ns	Measured at 50%, $V_L = V_H = +0.4 \text{ V}$, $V_{TERM} = -0.4 \text{ V}$
Overshoot and Preshoot	-3.0 + 75		+3.0 + 75	% of Step + mV	V_{H}/V_{L} , $V_{TERM} = (+0.4 \text{ V}, -0.4 \text{ V}), (0.0 \text{ V}, -2.0 \text{ V}),$
					(0.0 V, +7.0 V)
V _{TERM} Mode Rise Time			4.0	ns	V_L , $V_H = 0$ V, $V_{TERM} = -2$ V, $20\%-80\%$
V _{TERM} Mode Fall Time			5.5	ns	V_L , $V_H = 0$ V, $V_{TERM} = -2$ V, $20\%-80\%$
PSRR, DRIVE or TERM Mode	35			dB	$V_S = V_S \pm 3\%$

Specifications subject to change without notice.

COMPARATOR SPECIFICATIONS

(All specifications are at $T_J = +85^{\circ}C \pm 5^{\circ}C$, $+V_S = +12 \text{ V} \pm 3\%$, $-V_S = -7 \text{ V} = \pm 3\%$ unless otherwise noted. All temperature coefficients are measured at $T_J = +75^{\circ}C$ to $+95^{\circ}C$).

Parameter	Min	Тур	Max	Units	Test Conditions
DC INPUT CHARACTERISTICS					
Offset Voltage (V _{OS})	-25		25	mV	CMV = 0 V
Offset Voltage (Drift)		50		μV/°C	CMV = 0 V
HCOMP, LCOMP Bias Current	-50		50	μA	$V_{IN} = 0 V$
Voltage Range (V _{CM})	-3		8.0	v	
Differential Voltage (V _{DIFF})			9.0	V	
Gain and Linearity	-0.05		0.05	% FSR	$V_{IN} = -3 V \text{ to } +8 V$
LATCH ENABLE INPUTS					
Logic "1" Current (I _{IH})			250	μΑ	LE, $\overline{\text{LE}} = -0.8 \text{ V}$
Logic "0" Current (I _{IL})	-250			μA	LE, $\overline{LE} = -1.8 \text{ V}$
DIGITAL OUTPUTS					
Logic "1" Voltage (V _{OH})	-0.98			V	Q or \overline{Q} , 50 Ω to -2 V
Logic "0" Voltage (Vol.)			-1.5	V	$O \text{ or } \overline{O}, 50 \Omega \text{ to } -2 \text{ V}$
Slew Rate		1		V/ns	
SWITCHING PERFORMANCE					
Propagation Delay					
Input to Output	0.9		2.5	ns	$V_{IN} = 2 V p-p,$
Latch Enable to Output		2		ns	HCOMP = +1 V, LCOMP = +1 V
Propagation Delay Temperature Coefficient		2		ps/°C	
Propagation Delay Change with Respect to					
Slew Rate: 0.5 V, 1.0 V, 3.0 V/ns		<±10	0	ps	$V_{IN} = 0 \text{ V to 5 V}$
Slew Rate: 5.0 V/ns		<±35	0	ps	$V_{IN} = 0 \text{ V to 5 V}$
Amplitude: 1.0 V, 3.0 V, 5.0 V		<±20	0	ps	$V_{IN} = 1.0 \text{ V/ns}$
Equivalent Input Rise Time		450		ps	$V_{IN} = 0 \text{ V to } 3 \text{ V}, 3 \text{ V/ns}$
Pulsewidth Linearity		<±20	0	ps	$V_{IN} = 0 \text{ V to } 3 \text{ V}, 3 \text{ V/ns}, PW = 3 \text{ ns} - 8 \text{ ns}$
Settling Time		<25		ns	Settling to ± 8 mV, $V_{IN} = 1$ V to 0 V
Latch Timing					
Input Pulsewidth		<1.5		ns	
Setup Time		<1.0		ns	
Hold Time		<1.0		ns	

Specifications subject to change without notice.

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AD53032—SPECIFICATIONS

ACTIVE LOAD SPECIFICATIONS

(All specifications are at $T_J = +85^{\circ}\text{C} \pm 5^{\circ}\text{C}$, $+V_S = +12 \text{ V} \pm 3\%$, $-V_S = -7 \text{ V} = \pm 3\%$ unless otherwise noted. All temperature coefficients are measured at $T_J = +75^{\circ}\text{C}$ to $+95^{\circ}\text{C}$).

Parameter	Min	Typ	Max	Units	Test Conditions
INPUT CHARACTERISTICS					
$\overline{\text{INH}}, \overline{\overline{\text{INHL}}}$					
Input Voltage	-2		0	V	IOHC = +1 V, IOLC = +1 V, VCOM = +2 V, VDUT = 0 V
Bias Current	-250		250	μА	$INHL$, $\overline{INHL} = -2 \text{ V}$, 0 V
IOHC Current Program Range					
IOH = 0 mA to -35 mA	0		3.5	V	VDUT = −1.7 V, +8 V
IOLC Current Program Range					
IOL = 0 mA to +35 mA	0		3.5	V	VDUT = -3 V, +6.7 V
IOHC, IOLC Input Bias Current	-300		300	μΑ	IOLC = 0 V, +3.5 V and $IOHC = 0 V, +3.5 V$
IOLRTN, IOHRTN Range	-3		8	V	IOL = +35 mA, IOH = -35 mA, VDUT = -3 V, +8 V
VDUT Range	-3		8	V	IOL = +35 mA, $IOH = -35 mA$, $IVDUT-VCOMI > 1.3 V$
VDUT Range, IOH = 0 mA to -35 mA	-1.7		8	V	VDUT –VCOM > 1.3 V
VDUT Range, $IOL = 0 \text{ mA to } +35 \text{ mA}$	-3		8	V	VCOM-VDUT > 1.3 V
VCOMI Input Range	-3		8	V	IOL = +35 mA, IOH = -35 mA
OUTPUT CHARACTERISTICS					
Accuracy					
Absolute Accuracy Error, Load Current	-0.4 - 20	00	+0.4 + 200	% I _{SET} + μA	IOL, IOH = 25 μ A-35 mA, VCOM = 0 V, VDUT = ± 2 V and
					IOL = $25 \mu A$ – $35 mA$, VCOM = $+8 V$, VDUT = $+6.7 V$ and
					IOH = 25 μ A-35 mA, VCOM = -3 V, VDUT = -1.7 V
VCOM Buffer					
Offset Error	-50		50	mV	IOL, $IOH = 35 mA$, $VCOMI = 0 V$
Bias Current	-10	1	10	μΑ	VCOMI = 0 V
Gain Error	-0.2		0.2	%	IOL, IOH = 35 mA, VCOMI = -2 V to $+7$ V
Linearity Error	-10		10	mV	IOL, IOH = 35 mA , VCOMI = -2 V to $+7 \text{ V}$
Output Current TC		<±2		μΑ/°C	Measured at IOH, IOL = 200 μA
DYNAMIC PERFORMANCE					
Propagation Delay					
±IMAX to Inhibit	0.8	1.5	2.5	ns	$VCOM = \pm 3 V$, $IOL = +20 mA$, $IOH = -20 mA$
Inhibit to ±IMAX	1.5	2.4	4.0	ns	$VCOM = \pm 3 V$, $IOL = +20 mA$, $IOH = 20 mA$
Propagation Delay Matching	-1.8		1.8	ns	
I/O Spike		<250		mV	VCOM = 0 V, $IOL = +20 mA$, $IOH = -20 mA$
Settling Time to 15 mV		< 50		ns	$IOL = +20 \text{ mA}$, $IOH = -20 \text{ mA}$, 50Ω Load, to 15 mV
Settling Time to 4 mV		<10		μs	$IOL = +20 \text{ mA}$, $IOH = -20 \text{ mA}$, 50Ω Load, to 4 mV

Specifications subject to change without notice.

TOTAL FUNCTION SPECIFICATIONS

(All specifications are at $T_1 = +85^{\circ}\text{C} \pm 5^{\circ}\text{C}$, $+V_S = +12 \text{ V} \pm 3\%$, $-V_S = -7 \text{ V} = \pm 3\%$ unless otherwise noted. All temperature coefficients are measured at $T_1 = +75^{\circ}\text{C}$ to $+95^{\circ}\text{C}$).

Parameter	Min	Тур	Max	Units	Test Conditions
OUTPUT CHARACTERISTICS					
Output Leakage Current, $V_{OUT} = -2 \text{ V to } +7 \text{ V}$	-500		+500	nA	
Output Leakage Current, $V_{OUT} = -3 \text{ V to } +8 \text{ V}$	-2		+2	μA	
Output Capacitance		8		pF	Driver and Load INHIBITED
POWER SUPPLIES					
Total Supply Range		19		V	
Positive Supply		12		V	
Negative Supply		-7		V	
Positive Supply Current			260	mA	Driver = I_{NH} , I_{LOAD} Program = 35 mA, Load = Active
Negative Supply Current			270	mA	Driver = I _{NH} , I _{LOAD} Program = 35 mA, Load = Active
Total Power Dissipation			5.0	W	Driver = I_{NH} , I_{LOAD} Program = 35 mA, Load = Active
Temperature Sensor Gain Factor		1		μA/K	$R_{LOAD} = 10 \text{ k}\Omega, V_{SOURCE} = +10 \text{ V}$

NOTES

Connecting or shorting the decoupling pins to ground will result in the destruction of the device. Specifications subject to change without notice.

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Table I. Driver Truth Table

DATA	DATA	IOD	ĪOD	RLD	RLD	OUTPUT STATE
0	1	1	0	X	X	VL
1	0	1	0	X	X	VH
X	X	0	1	0	1	INH
X	X	0	1	1	0	VTERM

Table II. Comparator Truth Table

						C	OUTPUT ST	ATES	
vou	U T	LEH	LEH	LEL	LEL	QH	$\overline{\mathbf{QH}}$	QL	$\overline{\mathbf{QL}}$
>HCOMP	>LCOMP	1	0	1	0	1	0	1	0
>HCOMP	<lcomp< td=""><td>1</td><td>0</td><td>1</td><td>0</td><td>1</td><td>0</td><td>0</td><td>1</td></lcomp<>	1	0	1	0	1	0	0	1
<hcomp< td=""><td>>LCOMP</td><td>1</td><td>0</td><td>1</td><td>0</td><td>0</td><td>1</td><td>1</td><td>0</td></hcomp<>	>LCOMP	1	0	1	0	0	1	1	0
<hcomp< td=""><td><lcomp< td=""><td>1</td><td>0</td><td>1</td><td>0</td><td>0</td><td>1</td><td>0</td><td>1</td></lcomp<></td></hcomp<>	<lcomp< td=""><td>1</td><td>0</td><td>1</td><td>0</td><td>0</td><td>1</td><td>0</td><td>1</td></lcomp<>	1	0	1	0	0	1	0	1
X	X	0	1	0	1	QH (t-1)	<u>QH</u> (t-1)	QL (t-1)	$\overline{\mathrm{QL}}$ (t-1)

Table III. Active Load Truth Table

			OUTPUT STATES (Including Diode Bridge)					
VDUT	INHL	INHL	ЮН	IOL	I(VOUT)			
<vcom< td=""><td>0</td><td>1</td><td>V(IOHC) × 10 mA</td><td>V(IOLC) × 10 mA</td><td>IOL</td></vcom<>	0	1	V(IOHC) × 10 mA	V(IOLC) × 10 mA	IOL			
>VCOM	0	1	$V(IOHC) \times 10 \text{ mA}$	$V(IOLC) \times 10 \text{ mA}$	IOH			
X	1	0	0	0	0			

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ABSOLUTE MAXIMUM RATINGS¹ Power Supply Voltage +V_S to GND+13 V PWR GND to ECL GND or HQ GND ±0.4 V DATA, \overline{DATA} , IOD, \overline{IOD} , RLD, \overline{RLD} +5 V, -3 V DATA to \overline{DATA} , IOD to \overline{IOD} , RLD to \overline{RLD} ± 3 V LEL, $\overline{\text{LEL}}$, LEH, $\overline{\text{LEH}}$ +5 V, -3 V LEL to $\overline{\text{LEL}}$, LEH to $\overline{\text{LEH}}$ $\pm 3 \text{ V}$ INHL, <u>INHL</u> +5 V, -3 V INHL to $\overline{\text{INHL}}$ $\pm 3 \text{ V}$ VH, VL, VTERM, VCOM_I to GND +9 V, -4 V (VH-VTERM) and (VTERM - VL)±11 V IOLC ±6 V HCOMP+9 V, -4 V HCOMP, LCOMP to V_{OUT} ±11 V V_{OUT} Short Circuit Duration Indefinite² V_{OUT} Inhibit Mode +9 V, -4 V VHDCPL Do Not Connect Except for Cap to V_{CC} VLDCPL Do Not Connect Except for Cap to VEE QH, QH, QL, QL Maximum IOUT THERM+13 V, 0 V IOHRTN, IOLRTN +8.5 V, -3.5 V

Environmental

Operating Temperature (Junction)	+175°C
Storage Temperature65°C to	+150°C
Lead Temperature (Soldering, 10 sec) ³	+260°C

NOTES

¹Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Absolute maximum limits apply individually, not in combination. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

²Output short circuit protection is guaranteed as long as proper heatsinking is employed to ensure compliance with the operating temperature limits.

Table IV. Package Thermal Characteristics

Air Flow, FM	θ _{JA} , °C/W
0	33
200	25
400	22

ORDERING GUIDE

Model	Package Description	Shipment Method Quantity per Shipping Container	Package Option
AD53032JSTP	52-Lead LQFP-EDQUAD	90	SQ-52

CAUTION_

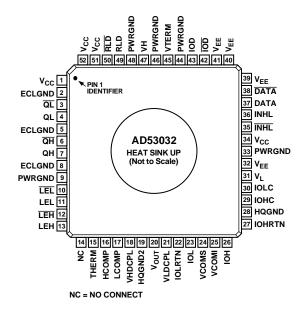
ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the AD53032 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



-6- REV. 0

 $^{^3}$ To ensure lead coplanarity (± 0.002 inches) and solderability, handling with bare hands should be avoided and the device should be stored in environments at 24°C ± 5 °C (75°F ± 10 °F) with relative humidity not to exceed 65%.

PIN CONFIGURATION

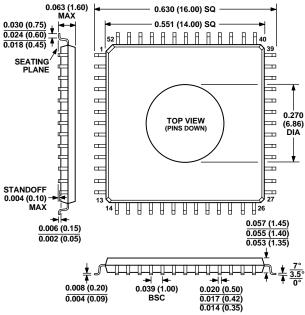


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OUTLINE DIMENSIONS

Dimensions shown in inches and (mm).

52-Lead LQFP-EDQUAD with Integral Heat Slug (SQ-52)



CENTER FIGURES ARE TYPICAL UNLESS OTHERWISE NOTED